I hereby certify that this correspondence is being deposited with the united states postal service as in an envelope addressed to: Commissioner of Patents, P.O.Box 1450, Alexandria, VA 22313, on November 12, 2003. The applicant and/or attorney requests the date of deposit as the filing date. Depositor: Karen Cinq-Mars

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(Signature & date)

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of :

November 12, 2003

Michael P. Belyansky et al.:

Group Art Unit:

Serial No. 10/605,857

Examiner:

Filed: 10/31/2003

**International Business Machines Corporation** 

2070 Route 52

Hopewell Junction, NY 12533

TITLE: HDP Process for High Aspect Ratio Gap Filling

## **INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the prior patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

Respectfully submitted,

Michael P. Belyansky et al.

BY

Steven Capella, Attorney Registration No. 33,086

Telephone No. 845-894-3669

INFORMATION DISCLOSURE CITATION					Docket Number (Optional)		Application Number			
					FIS920030085US1 10/605,857  Applicant(s)  Michael B. Belvensky et al.					
NOV 1	4 2003	(Use several sheets if necessor	ary)	Michael P. Belyansky et al.  Filing Date Group Art Unit						
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Form PTO-A820 (also form PTO-1449)